

ABSTRACT

The present disclosure aims to provide a technology capable of etching a film at least containing Si and N in a substrate having a film at least containing Si and O and the film at least containing Si and N while suppressing etching of the film at least containing Si and O. The present disclosure relates to an etching method including bringing (I) HF gas and (II) at least one compound selected from the group consisting of a sulfonyl compound, a carbonyl compound, a sulfonyl isocyanate compound, and an isocyanate compound into contact with a substrate having a film at least containing Si and O and a film at least containing Si and N to etch the film at least containing Si and N.